

Publisher Correction: Enhanced ferroelectricity in ultrathin films grown directly on silicon

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 Check for updates

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In the first sentence of this Article, “Ultrathin ferroelectric materials could potentially enable low-power **perovskite ferroelectric tetragonality** logic and nonvolatile memories”, the words “perovskite ferroelectric tetragonality” should not have appeared. This error has been corrected online.